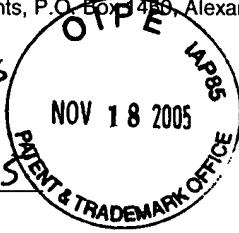


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Depositor: ROBERT FABER

Robert Faber 11-10-05
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of _____ :

Cheng, et al. : Group Art Unit: 2822

Serial No: 10/605,227 : Examiner: Kiesha L. Rose

Filed: 9/16/03 : International Business Machines Corporation
2070 Route 52
Hopewell Junction, NY 12533

TITLE: STRUCTURE OF VERTICAL STRAINED SILICON DEVICES

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or non-pertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted,
Cheng, et al.

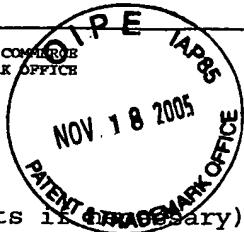
By

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F15920030221US1
F15920050492US4

applicant.

Form PTO-1449 (REV. 7-80) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		Atty. Docket No. FIS920030221US1	Serial No. 10/605,227
LIST OF PRIOR ART CITED BY APPLICANT (Use several sheets if necessary)		Applicants Cheng, et al.	
		Filing Date 9/16/03	Group Art Unit 2822

**OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)**

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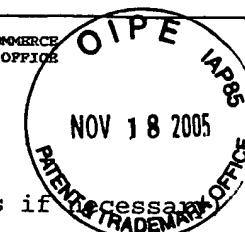
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Atty. Docket No.

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